

April 19, 2011

Santa Clara, CA – The U.S. Patent and Trademark Office granted Multibeam Corporation another key patent. US Patent #7,928,404 was issued to Multibeam on April 19, 2011. The patent covers a method to blank and unblank an electron beam with high speed and low blur, enabling faster and more precise Electron-Beam Lithography (EBL).

Multibeam's all-electrostatic e-beam columns are small, extremely fast and low-cost. Our multi-column architecture scales for high throughput. By complementing optical lithography, Multibeam's Complementary EBL (CEBL) enables the most cost-efficient production of next-generation microchips in high volumes.

Multibeam has 15 patents granted in the United States, as well as a pipeline of patents pending. In addition to its patent portfolio, Multibeam has completed substantial research, development and engineering in high-resolution low-cost e-beam columns, as well as multiple-column architectures.

About Multibeam Corporation

Multibeam is the technology leader in high-speed multiple-column E-Beam Lithography (EBL). In 2011, Multibeam introduced Complementary EBL (CEBL). CEBL extends Optical Lithography and enables the production of next-generation semiconductors in high volumes at reduced cost. Multibeam is led by Dr. David K. Lam, founder and former CEO of Lam Research Corporation. More information is available at www.multibeamcorp.com.

Contact: Ted Prescop (408) 980-1800 x3 info@multibeamcorp.com